Reg. No.

Question Paper Code : 80335

B.E./B.Tech. DEGREE EXAMINATION, NOVEMBER/DECEMBER 2016.

Third Semester

Electronics and Communication Engineering

EC 6304 – ELECTRONIC CIRCUITS - I

(Regulations 2013)

Time : Three hours

Maximum : 100 marks

Answer ALL questions.

PART A — $(10 \times 2 = 20 \text{ marks})$

1. What is a Q point?

2. What is the impact of temperature on drain current of MOSFET?

3. What is an ac load line?

4. Draw the small-signal ac equivalent circuit of the BJT.

5. What is the impact of including a source resistor in the FET amplifier?

6. Why multi-stage amplifiers are required?

- 7. What is the reason for reduction in gain at lower and higher frequencies in case of amplifiers?
- 8. Determine the unity-gain bandwidth of a FET with parameters, Cgd = 10 fF, Cgs = 50 fF and $g_m = 1.2$ mA/V.

9. Why active loads are not used with discrete circuits?

10. Define CMRR.

PART B — $(5 \times 13 = 65 \text{ marks})$

11. (a) Analyze a BJT with a voltage divider bias circuit, and determine the change in the Q-point with a variation in β when the circuit contains an emitter resistor. Let the biasing resistors be $R_{B1} = 56 k \Omega$, $R_{B2} = 12.2 k \Omega$, $R_{C} = 2 K \Omega$, $R_{E} = 0.4 k \Omega$, $V_{CC} = 10 V$, $V_{BE}(on) = 0.7 V$, and $\beta = 100$.

(b) Consider the circuit shown below with transistor parameters I_{DSS}=12 mA, $V_P = -4V$, and $\lambda = 0.008 V^{-1}$. Determine the small-signal voltage gain $A_v = vo/vi$.



12. (a) Analyze a basic common-base amplifier circuit and derive the expressions for its small-signal voltage gain, current gain, input impedance and output impedance.

Or

- (b) With neat diagrams, explain the operation and advantages of Darlington pair circuit. Also analyze its small-signal voltage gain and input impedance.
- 13. (a) Determine the small-signal voltage gain of a multistage cascade circuit shown in the figure below. The transistor parameters are $K_{n1} = 0.5 \text{ mA/V}^2$, $K_{n2} = 0.2 \text{ mA/V}^2$, $V_{TN1}=V_{TN2}=1.2 \text{ V}$ and $\lambda_1 = \lambda_2 = 0$. The quiescent drain currents are $I_{D1} = 0.2 \text{ mA}$ and $I_{D2} = 0.5 \text{ mA}$.



Or

2

80335

- (b) (i) Draw the circuit of a basic common source amplifier with voltage divider bias and derive the expressions for voltage gain, input impedance and output impedance using small-signal model. (8)
 - (ii) Determine the voltage gain of the circuit, assuming the following parameters: $V_{DD} = 3.3 \text{ V}$, $R_{D} = 10 \text{ k}\Omega$, $R_{G1} = 140 \text{ k}\Omega$, $R_{G2} = 60 \text{ k}\Omega$, and $R_{Si} = 4 \text{ k}\Omega$. The transistor parameters are: $V_{TN} = 0.4 \text{ V}$, $K_n = 0.5 \text{ mA/V}^2$, and $\lambda = 0.02 V^{-1}$. (5)
- 14. (a) Derive the expression for cut-off frequency of a BJT.

Or

- (b) Construct the high frequency equivalent circuit of a MOSFET from its geometry and derive the expression for short circuit current gain in the common-source configuration.
- 15. (a) Draw and explain the operation of a simple MOSFET amplifier with active load and derive its voltage gain using small-signal equivalent circuit.

Or

(b) With necessary diagrams, explain the operation of a CMOS differential amplifier. Using small signal analysis, derive the expression for its voltage gain.

PART C —
$$(1 \times 15 = 15 \text{ marks})$$

(Application/Design/Analysis/Evaluation/Creativity/Case study)

16. (a) Design the circuit given below such that $I_{DQ} = 100 \ \mu A$, $V_{SDQ} = 3V$, and $V_{RS} = 0.8V$. Note that V_{RS} is the voltage across the source resistor R_S . The value of the larger bias resistor, either R_1 or R_2 is to be 200 $k\Omega$. Transistor parameter values are $Kp = 100 \ \mu A/V^2$ and $V_{TP} = -0.4V$. The conduction parameter, Kp may vary by ± 5 percent.



80335

- (b)
- Design the cascode circuit shown below to meet the following specifications: $V_{CE1} = V_{CE2} = 2.5 V, V_{RE} = 0.7 V, I_{C1} \cong I_{C2} \cong 1 mA$, and $I_{R1} \cong I_{R2} \cong I_{R3} = 0.10 mA$.



4